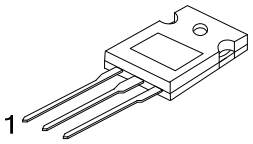
UNA15R090H

POWER MOSFET

171A, 150V N-CHANNEL ENHANCEMENT MODE TRENCH POWER MOSFET



TO-247

■ DESCRIPTION

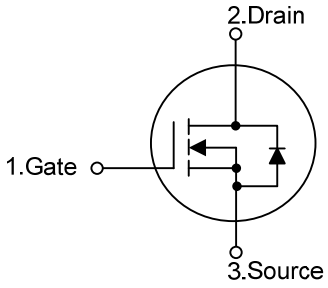
The UTC **UNA15R090H** is a N-channel enhancement mode power MOSFET using UTC's advanced technology to provide customers with ideal for low voltage inverter applications.

The UTC **UNA15R090H** is suitable for high efficiency synchronous rectification in SMPS, UPS, hard switched and high frequency circuits.

■ FEATURES

* $R_{DS(ON)}$ < 9.0 mΩ @ V_{GS}=10V, I_D=120A
* High Cell Density Trench Technology
* High Power and Current Handling Capability

■ SYMBOL



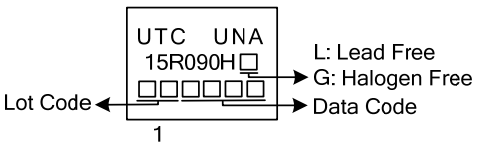
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UNA15R090HL-T47-T	UNA15R090HG-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

UNA15R090HG-T47-T (1)Packing Type	(1) T: Tube
(2)Package Type	(2) T47: TO-247
(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	150	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	Continuous	I_D	171	A
Pulsed Drain Current	Pulsed (Note 2)	I_{DM}	684	A
Peak Diode Recovery dv/dt (Note 4)		dv/dt	18.5	V/nS
Power Dissipation		P_D	517	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. I_{SD} ≤103A, di/dt ≤200A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_J = 25°C.

■ THERMAL CHARACTERISTICS

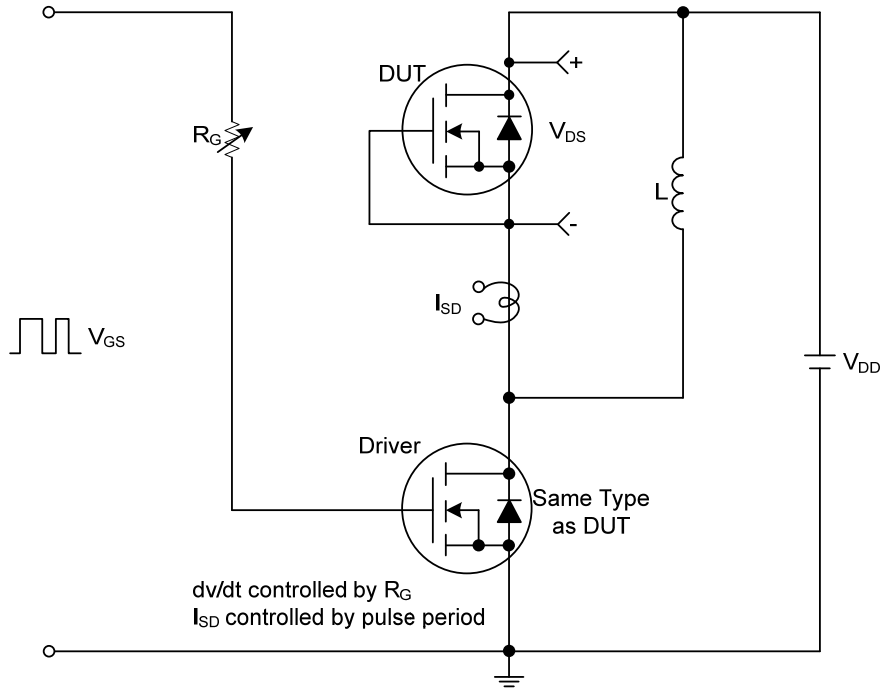
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	40	°C/W
Junction to Case	θ_{JC}	0.29	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified)

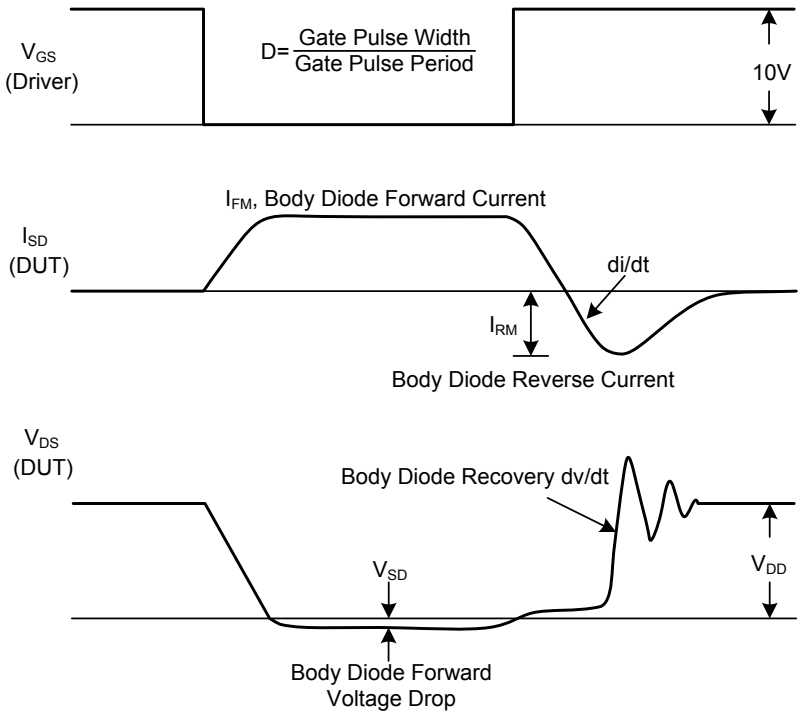
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	150			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=150V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	1.5		3.5	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=120A			9.0	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1.0MHz		20700		pF
Output Capacitance		C_{OSS}			1510		pF
Reverse Transfer Capacitance		C_{RSS}			445		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=120V, V_{GS}=10V, I_D=37.5A (Note 1, 2)		320		nC
Gate to Source Charge		Q_{GS}			98		nC
Gate to Drain Charge		Q_{GD}			74		nC
Turn-on Delay Time (Note 1)		$t_{D(ON)}$	V_{DS}=75V, V_{GS}=10V, I_D=37.5A R_G=4.7Ω (Note 1, 2)		45		ns
Rise Time		t_R			42		ns
Turn-off Delay Time		$t_{D(OFF)}$			235		ns
Fall-Time		t_F			137		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				171	A
Maximum Body-Diode Pulsed Current		I_{SM}				684	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S=103A, V_{GS}=0V			1.3	V
Reverse Recovery Time (Note 1)		t_{rr}	I_S=30A, V_{GS}=0V, di/dt=100A/μS		108		nS
Reverse Recovery Charge		Q_{rr}			448		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle≤2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



Peak Diode Recovery dv/dt Test Circuit



Peak Diode Recovery dv/dt Test Circuit and Waveforms

Peak Diode Recovery dv/dt Waveforms

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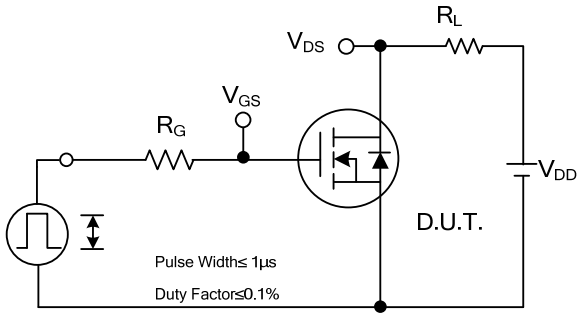
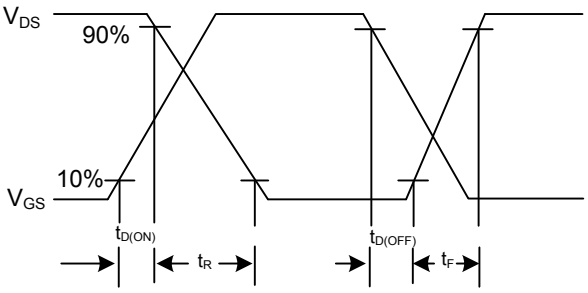
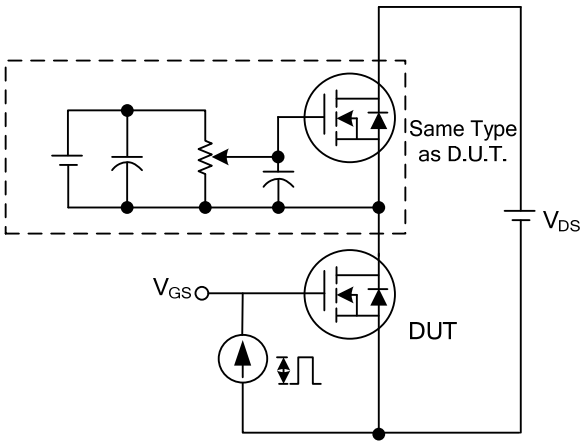


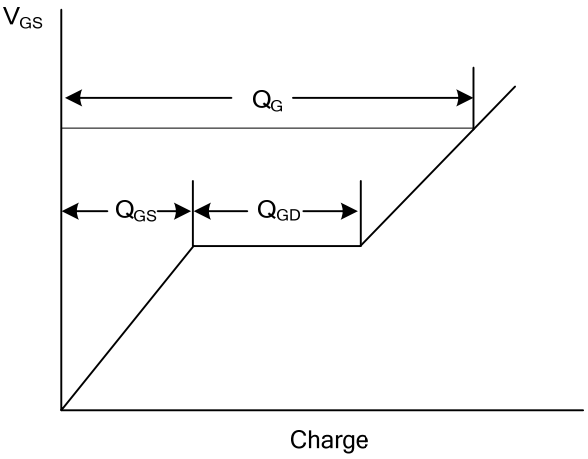
Switching Test Circuit



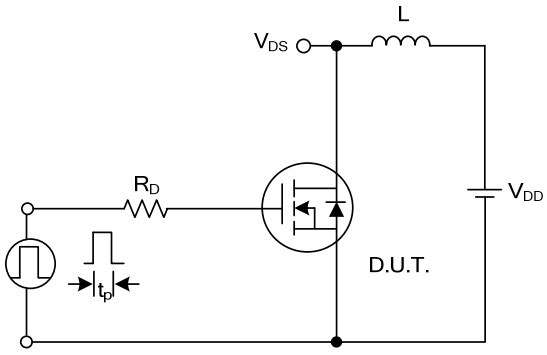
Switching Waveforms



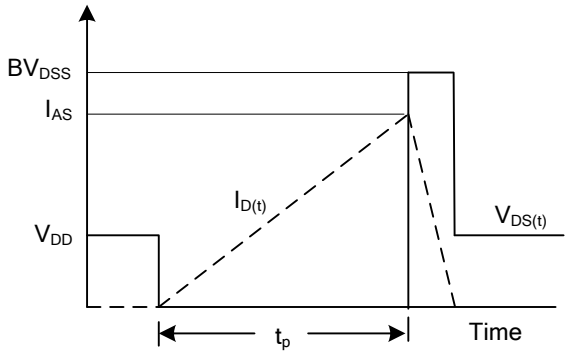
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms